SANYO

No.1207A

2SC3277

NPN Triple Diffused Planar Silicon Transistor
FOR SWITCHING REGULATORS

Features

- . High breakdown voltage, high current.
- . Wige ASO.
- . Fast switching speed.

Absolute Maximum Ratings at Ta	=25 ⁰ C				unit
Collector-to-Base Voltage	v_{CBO}			500	V
Collector-to-Emitter Voltage	ACEO			400	V ·
Emitter-to-Base Voltage	v_{EBO}			7	v
Collector Current	IC	- 1		10	A
Peak Collector	icp	PW≦300µs,		20	A
	- •	Duty Cycle≤10%			
Collector Dissipation	$P_{\mathbb{C}}$	Tc=25 ^O C		90	
Junction Temperature	Τj	•		150	°C
Storage Temperature	Tstg		-55 to	+150	°C

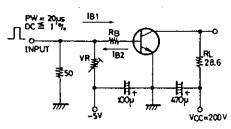
Electrical Characteristics at Collector Cutoff Current Emitter Cutoff Current	Ta=25°C I _{CBO} I _{EBO}	V _{CB} =400V,I _E =0 V _{EB} =5V,I _C =0	min	typ	max 10	unit. µA µA
DC Current Gain	h _{FE} (1) h _{FE} (2)	V _{CE} =5V,I _C =1.2A V _{CE} =5V,I _C =6A	15 * 8	ı	50 4	•
Gain-Bandwidth Product	$\mathbf{f}_{\mathbf{T}}^{\mathbf{r}}$	$V_{CE} = 10V, I_{C} = 1.2A$		20		\mathtt{MHz}
Output Capacitance	cob	$V_{CR} = 10V, f = 1MHz$		120		pF
C-E Saturation Voltage	VCE(sat)	$I_{C}=6A,I_{B}=1.2A$			1.0	V
B-E Saturation Voltage	VBE(sat)	$I_C=6A,I_B=1.2A$			1.5	v
C-B Breakdown Voltage	V(BR)CBO	$I_C = 1 \text{mA}, I_E = 0$	500			V
C-E Breakdown Voltage	V(BR)CEO	$I_C = 5 \text{mA}, R_{BE} = \infty$	400			V
E-B Breakdown Voltage	V(BR)EBO	$I_E = 1 \text{mA}, I_C = 0$. 7			V
C-E Sustain Voltage	V _{CEO(sus)}	I _C =10A, I _B =2A, L=50µH	400			V

Continued on next page. *: The $h_{FE(1)}$ of the 2SC3277 is classified as follows. When speitifying the $h_{FE(1)}$ rank, specity two ranks or more in principle.

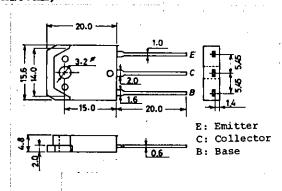
15 L 30 20 M 40 30 N 50

Package Dimensions 2022 (unit:mm)

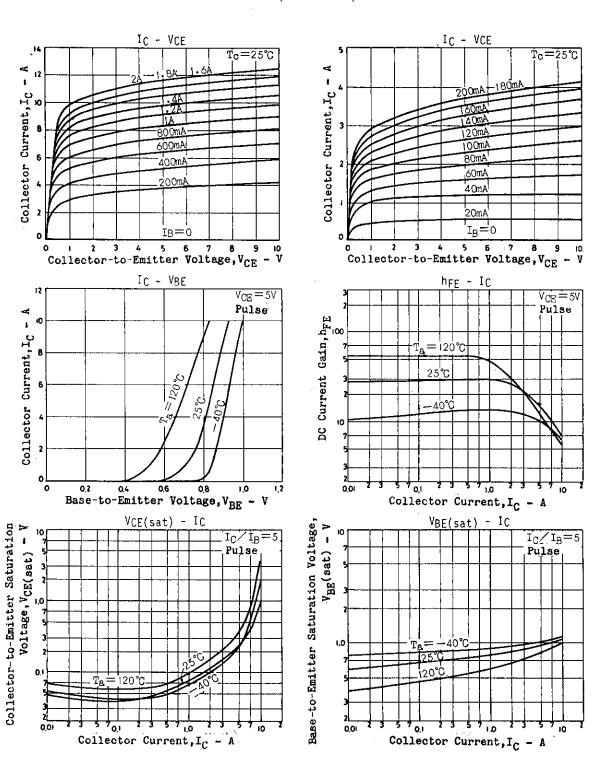
Switching Time Test Circuit

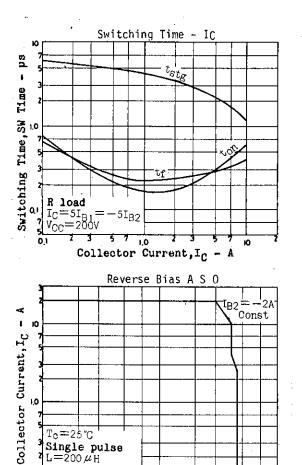


Unit (Resistance : Ω, Capacitance : F)



Continued from preced	ing page.	•					
				min	typ	max	unit
C-E Sustain Voltage	VCEX(sus)	I _C =10A,I _B I _{R2} =-2A,c	η=2A,L=200μΗ, lamped	400			V
C-E Sustain Voltage	V _{CEX} (sus)	I _C =2.5A,I ₁ I _{B2} =-0.5A	_{R1} =0.5A,L=200μH,	450			V
Turn-ON Time	ton	$I_{C}^{E_{2}}7A, I_{B_{1}}$ $R_{t} = 28.60 \text{ hm}$	=1.4A,I _{B2} =-1.4A, ns,V _{CC} =200V			1.0	μs
Storage Time		T H	11			2.5	นธ
Fall Time	tstg t _f	ti	ti			1.0	μs

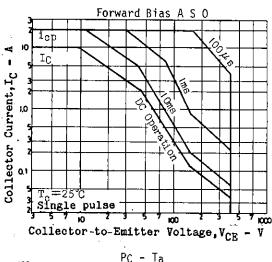


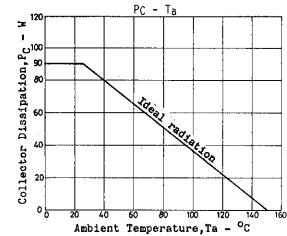


Collector-to-Emitter Voltage, VCE

 $=51_{B1}=$

0,1





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